

Experience using the HiCUM Master Toolkit

June 18th 2007

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- □ Project Background
- □ Project Challenges
- **☐** Summary of Results
- ☐ Feedback on the HMT Tool/issues
- ☐ Feedback on New Features



Project Background

Reason for evaluation:

- Improved high current ft modeling for SiGe NPNs
- □ Leverage HMT for geometric scaling

HMT evaluation

Technology: RF SiGe NPN – 50GHz, 0.25μm

Configurations: CBEBC, CBEB, CBE

Current compact model: VBIC (geometry specific models)

Simulation Tool: spectre



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Project Challenges

- Developing expertise in the HICUM Master Toolkit flow
- ☐ Test structures for technology were not developed with HiCUM geometric scaling in mind.
 - Technology has fixed emitter width
 - □ No test structures with varied width
 - □ Test structures available include fixed emitter width and 4 different lengths
 - □ No large arrays available to characterize depletion caps very accurately
 - Tetrode structures with various widths but fixed length
 - Sheet resistance of base link was taken from TCAD simulations as structures were not available for determination of base link resistance
- HMT Limitations not much flexibility for data input
 - Bias conditions, sweep orders
 - □ S parameters must be de-embedded for HMT input



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Summary of Results

- \Box Fixed emitter widths lead to small perimeter to area variation -> effects accuracy of γ_C and γ_B extractions
- □ Use of long tetrode only -> uncorrected, underestimate RSBi0 by a factor of 10 20%, still gives correct value for Qp0
- Accurate capacitance splitting not possible



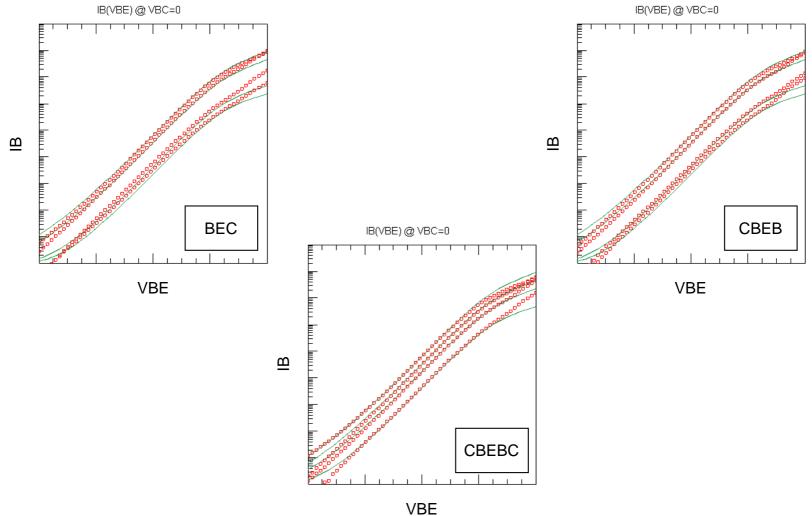
The lack of data will lead to some limitations!



Opportunity to encounter potential issues before a new test chip design is launched!

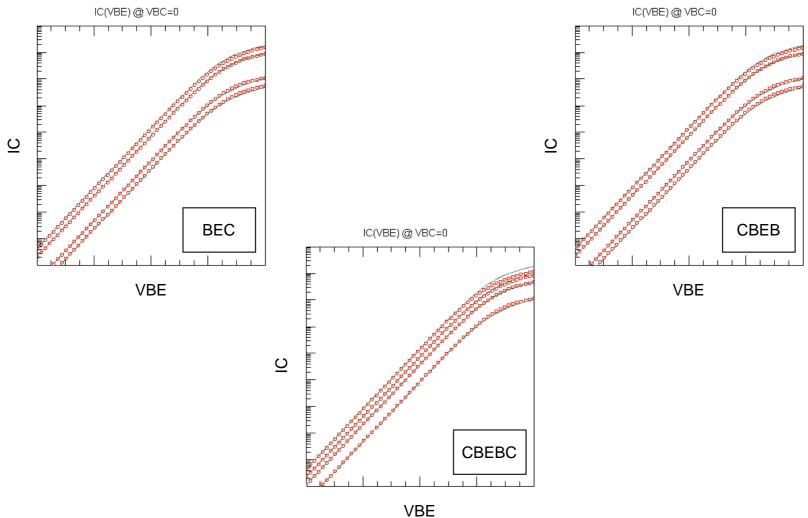


Summary of Results - IB



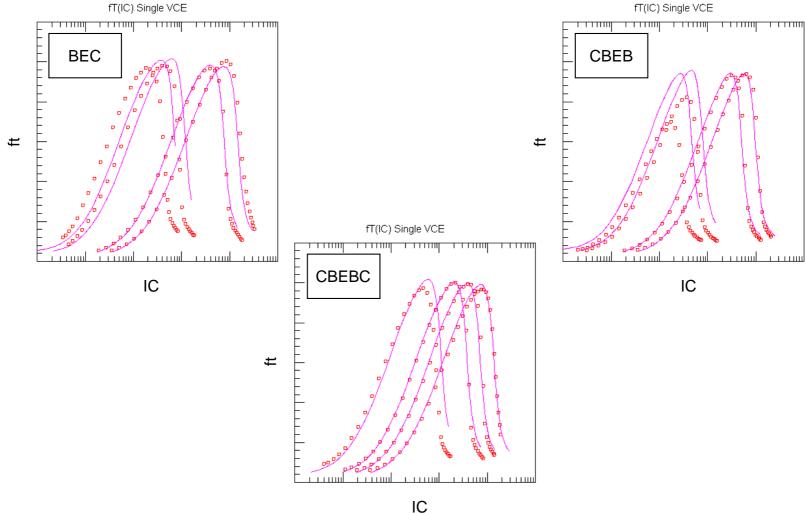


Summary of Results - IC



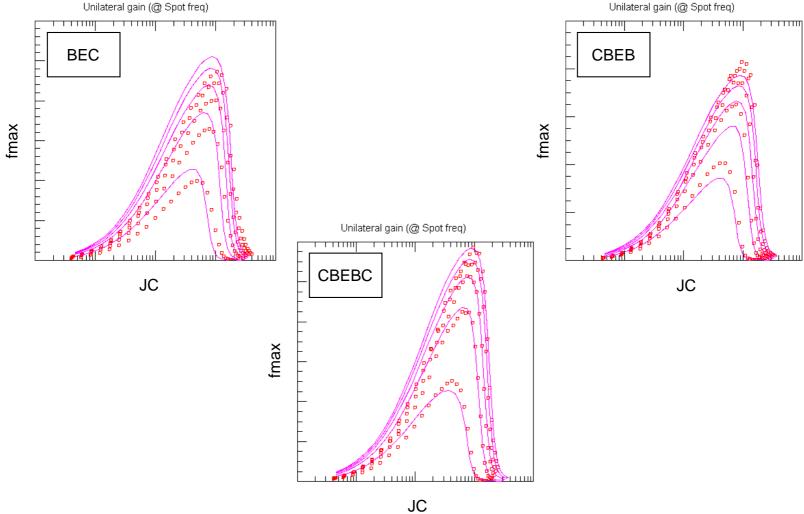


Summary of Results - ft





Summary of Results - fmax





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Feedback on HMT Tool/issues(1)

Circuit deck syntax incompatibility with spectre native format

```
define backend (C B E S)
C:CBEBE B E C=1e-20
C:CBCBE B C C=1e-20
HMT_FT:X1 C B E S
end backend

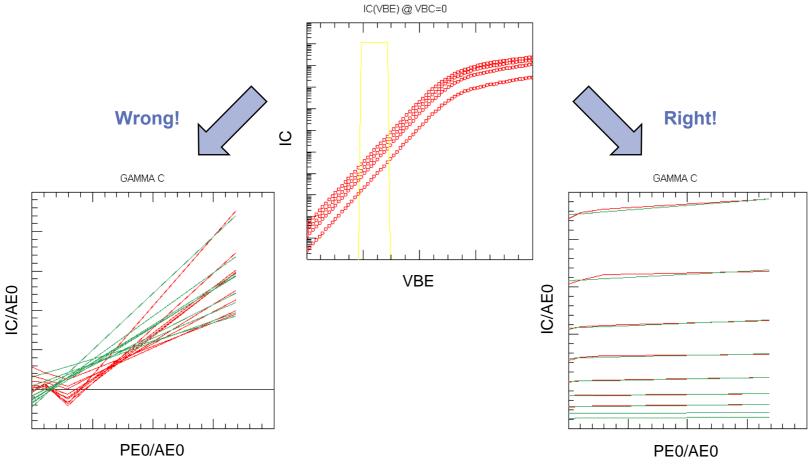
subckt backend (C B E S)
CBEBE B E capacitor C=1e-20
CBCBE B C capacitor C=1e-20
X1 C B E S HMT_FT
ends
```

- Load data: subcircuit in HMT_XX/DATA is updated with ADS syntax (the default), ICCAP automatically runs syntax parser -> error message
- <u>Simulation</u>: subcircuit is automatically replaced by HMT with spectre syntax. ICCAP makes automatic check for subcircuit parameters -> error message



Feedback on HMT Tool/issues(2)

 \blacksquare Extraction of γ_C and γ_B doesn't work, field table values are not set correctly

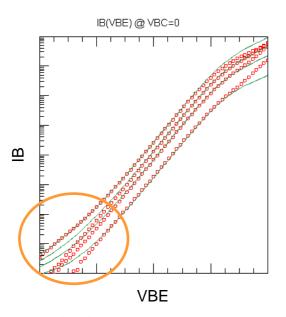


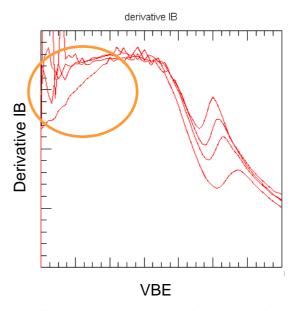


Feedback on HMT Tool/issues(3)

■ More flexibility is desired

- Support for different plots would require change in HMT code -> difficult
- Example: IB and first order derivative of IB to identify non-ideality range





- Biasing and sweep orders for input data are fixed, de-embedding outside the tool
- Additional extraction steps, e.g. to extract reverse characteristics

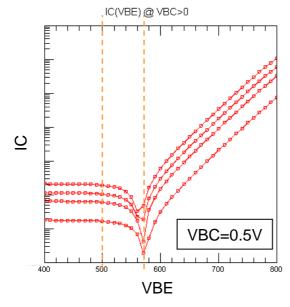


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Feedback on new features(1)

- □ Feedback from National's Analog designers an accurate model of reverse characteristics is important, because:
 - BJT must operate very close to saturation, gets more important as supply voltages shrink
 - Saturation considered as superposition of forward active and reverse active

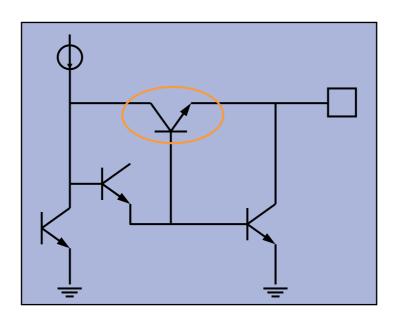


- Measurement precision issue for IBC extraction
- Shift in VBE



Feedback on new features(2)

- ☐ An accurate model of reverse characteristics is important, because:
 - □ To minimize current flow in overdrive, subcircuits are employed by designers (saturation limit circuits)
 - □ Require use of a sensing transistor to go into reverse active mode when sensed output stage device approaches saturation





Feedback on new features (3)

- □ Integration of scaling equations into Cadence design environment, so that <u>discrete model cards do not need to be generated</u>
 - Equations could be passed into netlist directly?
- ☐ Plan to evaluate on Complementary Vertical PNP transistors
 - Anyone else has extraction experience using HMT on CVPNPs?
- ☐ HiCUM Workshop planned in North America?

